

Active Bias Controller

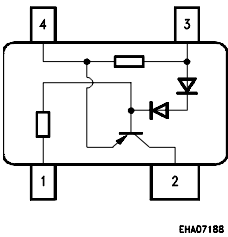
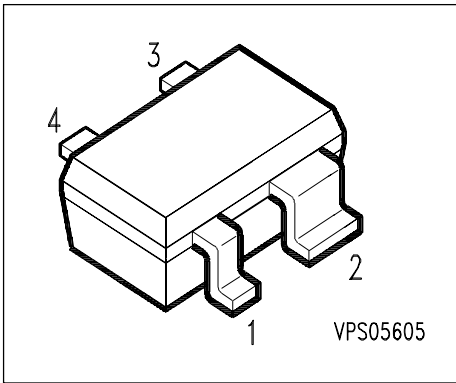
Characteristics

- Supplies stable bias current even at low battery voltage and extreme ambient temperature variation

- Low voltage drop of 0.7V

Application notes

- Stabilizing bias current of NPN transistors and FETs from less than 0.2mA up to more than 200mA
- Ideal supplement for SIEGET and other RF transistors
- also usable as current source up to 5mA



Type	Marking	Ordering Code	Pin Configuration				Package
BCR 400W	W4s	Q62702-C2481	1 GND/E _{NPN}	2 Contr/B _{NPN}	3 V _S	4 Rext/C _{NPN}	SOT-343

(E_{NPN}, B_{NPN}, C_{NPN} are electrodes of a stabilized NPN transistor)

Maximum Ratings

Parameter	Symbol	Values	Unit
Supply voltage	V _S	18	V
Control current	I _{Contr.}	10	mA
Control voltage	V _{Contr.}	16	V
Reverse voltage between all terminals	V _R	0.5	
Total power dissipation, T _S = 117°C	P _{tot}	330	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	- 65 ... + 150	

Thermal Resistance

Junction ambient ¹⁾	R _{thJA}	≤ 170	K/W
Junction - soldering point	R _{thJS}	≤ 100	

1) Package mounted on pcb 40mm x 40mm x 1.5mm / 6cm² Cu

Electrical Characteristics at $T_A=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

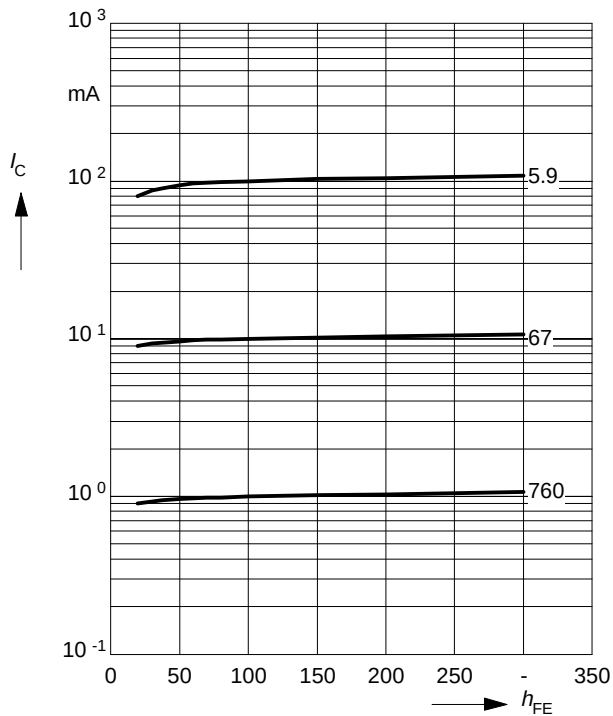
Additional current consumption $V_S = 3\text{ V}$	I_0	-	20	40	μA
Lowest stabilizing current $V_S = 3\text{ V}$	$I_{\min}$	-	0.1	-	mA

DC Characteristics with stabilized NPN-Transistors

Lowest sufficient battery voltage $I_B (\text{NPN}) < 0.5\text{ mA}$	$V_{S\min}$	-	1.6	-	V
Voltage drop ($V_S - V_{CE}$) $I_C = 25\text{ mA}$	V_{drop}	-	0.65	-	
Change of I_C versus h_{FE} $h_{FE} > 50$	$\Delta I_C / I_C$	-	0.08	-	$\Delta h_{FE} / h_{FE}$
Change of I_C versus V_S $V_S > 3\text{ V}$	$\Delta I_C / I_C$	-	0.15	-	$\Delta V_S / V_S$
Change of I_C versus T_A	$\Delta I_C / I_C$	-	0.2	-	%/K

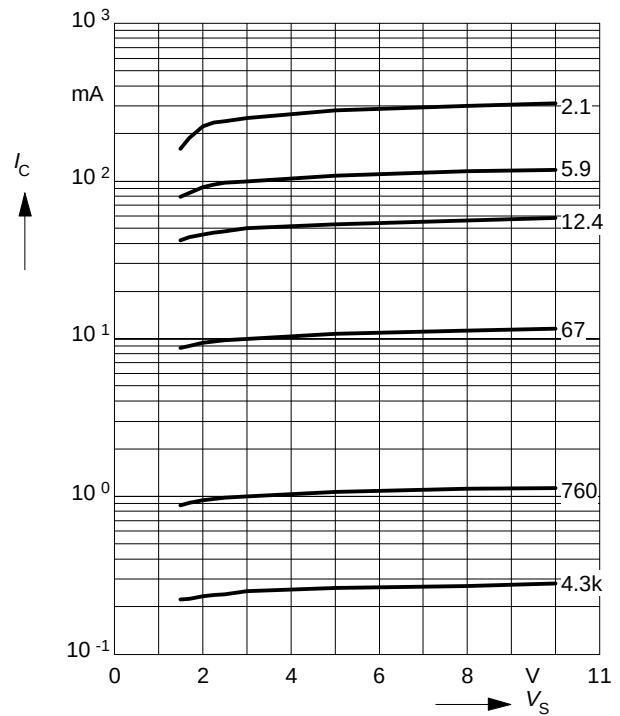
Collector current $I_C = f(h_{FE})$

I_C and h_{FE} refer to stabilized NPN Transistor
Parameter $R_{ext.} (\Omega)$

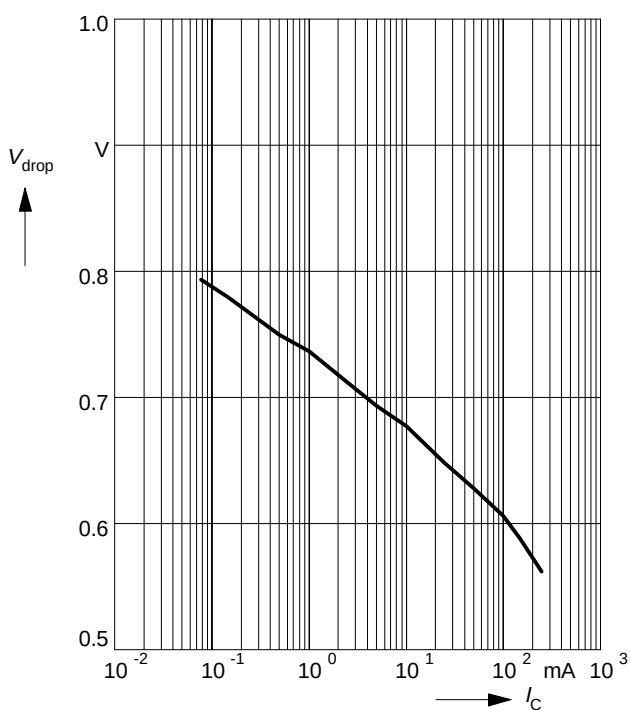


Collector Current $I_C = f(V_S)$

of stabilized NPN Transistor
Parameter $R_{ext.} (\Omega)$

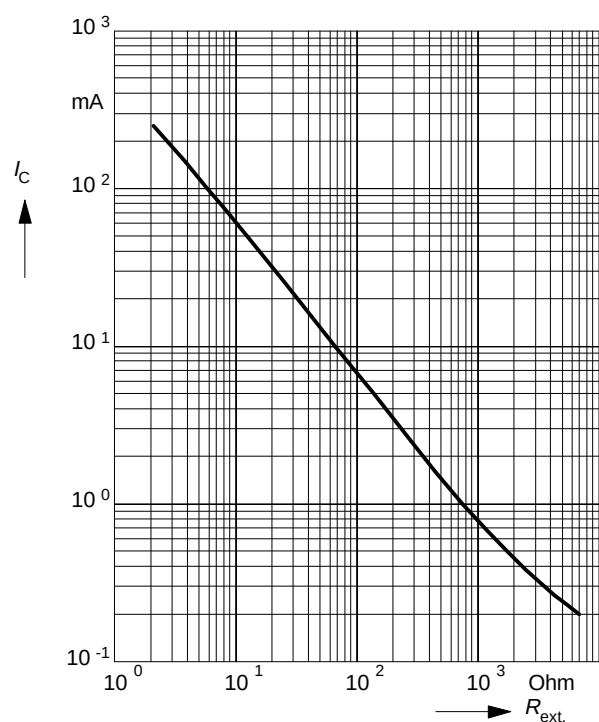


Voltage drop $V_{drop} = f(I_C)$

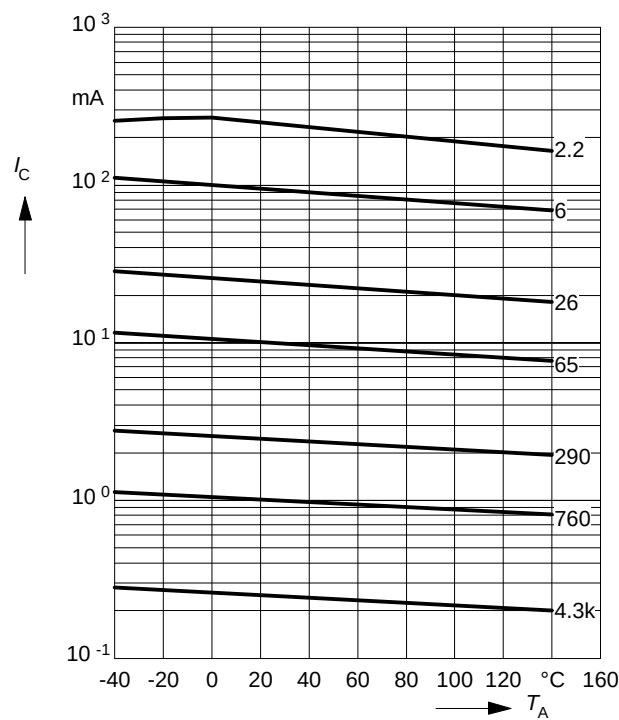


Collector current $I_C = f(R_{ext.})$

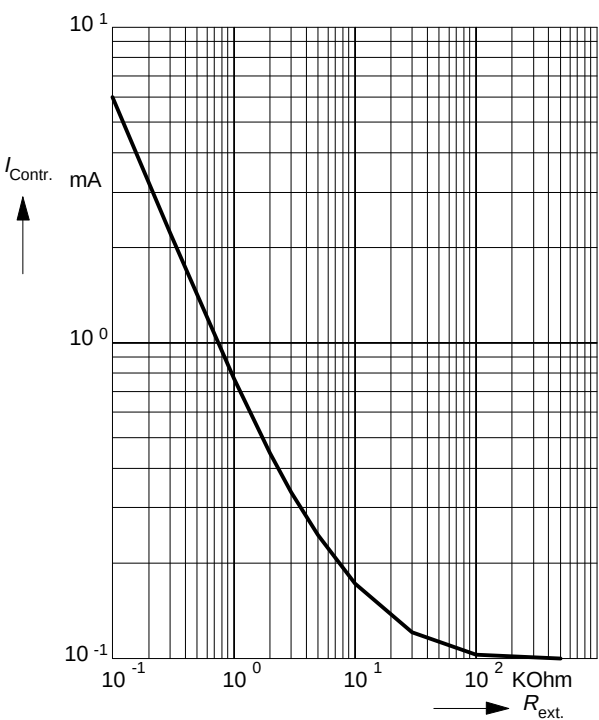
of stabilized NPN Transistor



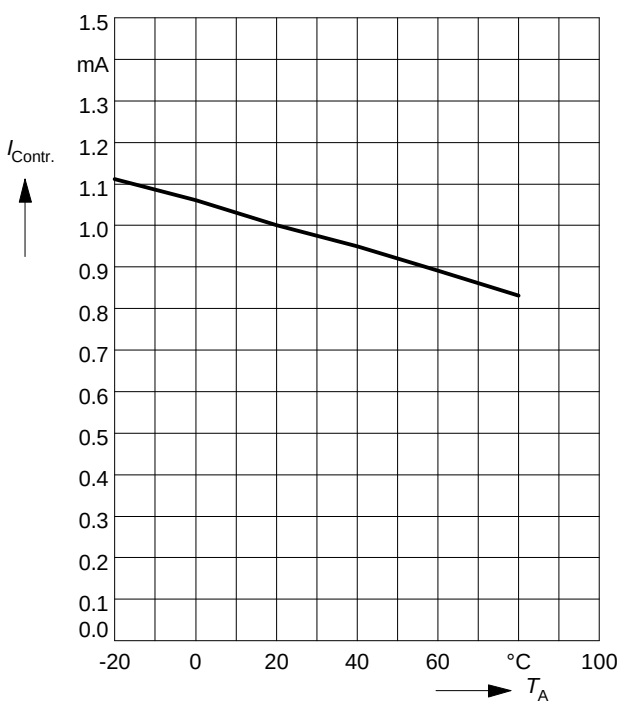
Collector current $T_A = f(I_C)$
of stabilized NPN Transistor
Parameter: $R_{ext.}(\Omega)$



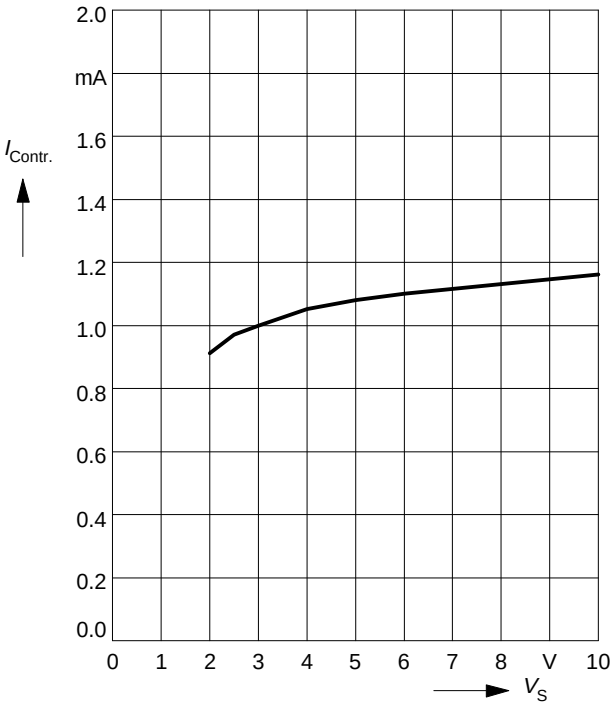
Control current $I = f(R_{ext.})$
in current source application



Control current $I = f(T_A)$
in current source application

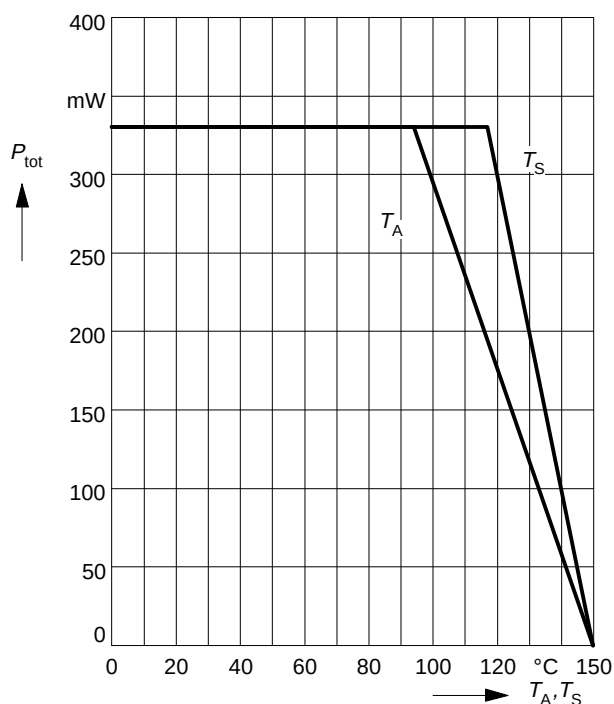


Control current $I = f(V_S)$
in current source application



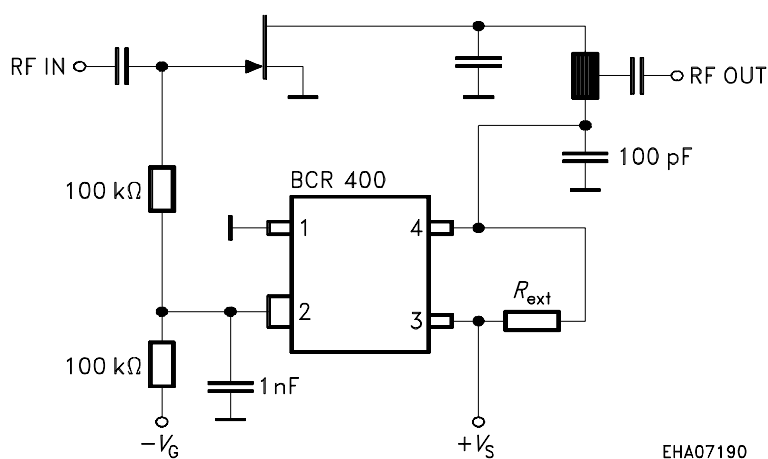
Total power dissipation $P_{\text{tot}} = f(T_A^*; T_S)$

* Package mounted on epoxy



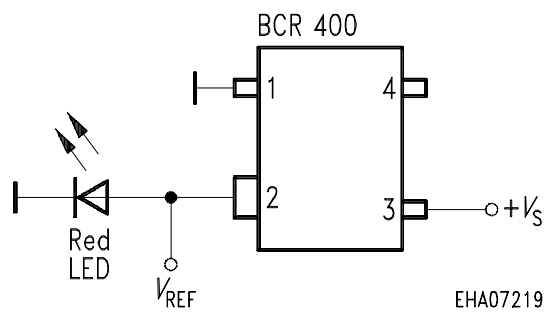
Note that up to $T_S = 130^\circ\text{C}$ it is not possible to exceed P_{tot} respecting the maximum ratings of V_S and I_{Contr} . The collector or drain current (respectively) of the stabilized RF transistor does not affect BCR 400 directly, as it provides just the base current.

Typical application for GaAs FET with active bias controller



EHA07190

Low voltage reference



Precision timer with BCR 400 providing constant charge current

